Abstracts

Characterization of source-to-drain capacitance (C/sub ds/) effect of GaAs PHEMT for millimeter wave switch

Younkyu Chung, Gi-Hyon Ryu, Dae-Hyun Kim, Jae-Hak Lee, Woo-Yeon Hong and Kwang-Seok Seo. "Characterization of source-to-drain capacitance (C/sub ds/) effect of GaAs PHEMT for millimeter wave switch." 2000 MTT-S International Microwave Symposium Digest 00.1 (2000 Vol. I [MWSYM]): 173-176.

This paper represents the device parameter influence of GaAs PHEMT with different gate lengths on switching performance and its application in DC-50GHz wide-band SPST monolithic switch ICs. From the characteristic of GaAs PHEMT and monolithic switch, especially, it is proved experimentally that source-to-drain capacitance dependent on gate length is a very important characteristic for improving the isolation performance of GaAs PHEMT switch at high-impedance state.

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